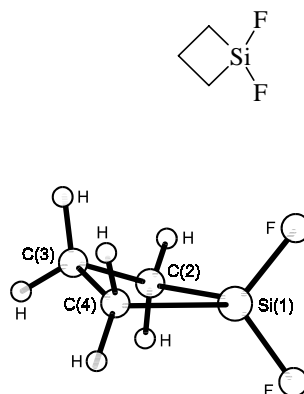


1251 **C₃H₆F₂Si**
 ED, *ab initio* calculations
 (HF/4-21G)

1,1-Difluorosilacyclobutane

C_s

r_a	\AA^a	θ_a	deg ^{a)}
Si–C	1.836(3)	C–Si–C	82.7(6)
C–C	1.574(8)	Si–C–C ^{b)}	86.8(8)
Si–F	1.574(3)	C–C–C ^{b)}	100.6(8)
C–H	1.099(6)	F–Si–F	106.9(5)
		H–C–H	111(3)
		ϕ^c	25(2)
		ρ (SiF ₂) ^{d)}	3.1 ^{e)}
		ρ (C(2)H ₂) ^{d)}	5.5 ^{e)}
		ρ (C(3)H ₂) ^{d)}	3.8 ^{e)}



The nozzle was at room temperature.

^{a)} Three times the estimated standard errors.

^{b)} Dependent parameter.

^{c)} Ring puckering angle: the dihedral angle between the CSiC and CCC planes.

^{d)} ρ is the rocking angle between the bisectors of adjacent exo- and endocyclic angles at the potential minimum. A positive value implies that the axial H or F atoms approach each other.

^{e)} Assumed.

Rempfer, B., Pfafferott, G., Oberhammer, H., Auner, N., Boggs, J.E.: *Acta Chem. Scand., Ser. A* **42** (1988) 352.